High-voltage Switching Transistor (Telephone, Power supply) (-600V, -1A)

2SA1807

Features

- 1) High breakdown voltage. (BVcEo=-600V)
- 2) Low saturation voltage, typically $V_{CE(sat)} = -0.25V$ at Ic / Is=-300mA / -60mA.
- 3) High switching speed, typically tf=0.4 μ s at Ic=-500mA
- 4) Wide SOA (safe operating area).

Packaging specifications and hre

Type	2SA1807
Package	CPT3
hre	NP
Code	TL
Basic ordering unit (pieces)	2500

●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	-600	V	
Collector-emitter voltage	VCEO	-600	V	
Emitter-base voltage	VEBO	-7	V	
Collector current	lc	-1	A (DC)	
	IC.	-2	A (Pulse) *	
Callagter newsy dissinction	Po	1	W	
Collector power dissipation	PC	10	W (Tc=25°C)	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*} Single pulse, Pw=100ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-600	_	_	V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVceo	-600	_	_	V	Ic=-1mA
Emitter-base breakdown voltage	ВУево	-7	_	_	V	I _E =-50 μ A
Collector cutoff current	Ісво	_	_	-10	μΑ	VcB=-600V
Emitter cutoff current	IEBO	_	_	-10	μΑ	VEB=-7V
Collector-emitter saturation voltage	VCE(sat)	_	-0.25	-1	V	Ic/Is=-300mA/-60mA
Base-emitter saturation voltage	VCE(sat)	_	_	-1.2	V	Ic/Is=-300mA/-60mA
DC current transfer ratio	hre	56	_	180	_	VcE=-5V, Ic=-100mA
Transition frequency	f⊤	_	15	_	MHz	VcB=-10V, IE=50mA, f=5MHz
Output capacitance	Cob	_	40	_	pF	Vc=-10V, I==0A, f=1MHz
Turn-on time	ton	_	0.2	_	μs	Ic=-500mA , RL=500 Ω
Storage time	tstg	_	1.8	_	μs	I _{B1} =-I _{B2} =-100mA
Fall time	tr	_	0.4	_	μs	Vcc <u>~</u> −250V

(96-102-A331)

High-voltage Switching Transistor (Telephone, Power supply) (-400V, -2A)

2SA1862

Features

- 1) High breakdown voltage. (BVcEo=-400V)
- 2) Low saturation voltage, typically VcE(sat) = -0.3V at lc / lb=-500mA / -100mA.
- 3) High switching speed, typically tf=0.4 μs at Ic=-1A.
- 4) Wide SOA (safe operating area).

Packaging specifications and hre

Туре	2\$A1862
Package	CPT3
hfE	Р
Code	TL
Basic ordering unit (pieces)	2500

●Absolute maximum ratings (Ta=25℃)

<u> </u>				
Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vcво	-400	V	
Collector-emitter voltage	Vceo	-400	V	
Emitter-base voltage	VEBO	— 7	V	
Collector current	lc	-2	A (DC)	
		-4	A (Pulse) *	
Collector power dissipation	Pc	1	W	
	PC	10	W (Tc=25°C)	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*} Single pulse, Pw=10ms

● Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-400	_	_	V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVceo	-400	_	_	V	Ic=-1mA
Emitter-base breakdown voltage	BVEBO	-7	_	_	V	IE=-50 μ A
Collector cutoff current	Ісво	_	_	-10	μΑ	VcB=-400V
Emitter cutoff current	Ієво	_	_	-10	μΑ	V _{EB} =-5V
Collector-emitter saturation voltage	VCE(sat)	_	-0.3	-0.5	V	Ic/Is=-0.5A/-0.1A
Base-emitter saturation voltage	VCE(sat)	_	_	-1.2	V	Ic/Is=-0.5A/-0.1A
DC current transfer ratio	hre	82	_	180	_	VcE=-5V, Ic=-0.1A
Transition frequency	f⊤	_	18	_	MHz	VoB=-10V, IE=0.1A, f=5MHz
Output capacitance	Cob	_	30	_	pF	Vce=-10V, le=0A, f=1MHz
Turn-on time	ton	_	0.2	_	μs	Ic=-1A , RL=150 Ω
Storage time	tstg	_	1.8	_	μs	$I_{B1} = -I_{B2} = -0.2A$
Fall time	tr	_	0.4	_	μ\$	Vcc <u>~</u> 150V

(96-109-A343)



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